F Yu Soldatenkov

List of Publications by Year
in descending order

35	238	1163117 8	1058476 14
papers	citations	h-index	g-index

35	35	35	172
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Polarization Spectroscopy of Anisotropic Plasmons in Selfâ€Oriented Nanoclusters of Gold on Monolayer of Nitrogen Atoms Chemisorbed at GaAs(001) Surface. Physica Status Solidi (B): Basic Research, 2022, 259, 2100394.	1.5	3
2	Au- and Ag-Containing Contacts to GaSb-Photovoltaic Converters. IEEE Electron Device Letters, 2022, 43, 418-421.	3.9	2
3	Deep level defects in GaAs gradual p-i-n junctions after neutron irradiation. Journal of Physics: Conference Series, 2022, 2227, 012019.	0.4	1
4	Dissimilar gold nanoclusters at GaAs(0Â0Â1) surface: Formation chemistry, structure, and localized plasmons. Applied Surface Science, 2020, 507, 144982.	6.1	6
5	Deep-level defects in high-voltage AlGaAs pâ€“iâ€“n diodes and the effect of these defects on the temperature dependence of the minority carrier lifetime. Journal of Applied Physics, 2020, 128, 095705.	2.5	4
6	Capacitance Spectroscopy of Heteroepitaxial AlGaAs/GaAs pâ€“iâ€“n Structures. Semiconductors, 2020, 54, 1260-1266.	0.5	1
7	Optical Spectroscopy of Schottky Nanostructures Au/GaAs: Plasmon Resonances and Anisotropy. Semiconductors, 2020, 54, 1877-1880.	0.5	3
8	Gold nanoclusters on GaAs(001) surface: atomic force microscopy and optical spectroscopy of plasmons. Journal of Physics: Conference Series, 2019, 1400, 055005.	0.4	0
9	Misfit dislocationâ€“related deep levels in InGaAs/GaAs and GaAsSb/GaAs pâ€“iâ€“n heterostructures and the effect of these on the relaxation time of nonequilibrium carriers. Journal of Applied Physics, 2018, 123, 161588.	2.5	7
10	Effect of Dislocation-related Deep Levels in Heteroepitaxial InGaAs/GaAs and GaAsSb/GaAs pâ€“iâ€“n Structures on the Relaxation time of Nonequilibrium Carriers. Semiconductors, 2018, 52, 165-171.	0.5	6
11	A Study of Ohmic Contacts of Power Photovoltaic Converters. Technical Physics Letters, 2018, 44, 1198-1200.	0.7	3
12	Gold Nanoclusters at the Interface Au/GaAs(001): Preparation, Characterization, and Plasmonic Spectroscopy. Semiconductors, 2018, 52, 1849-1852.	0.5	3
13	Annealing atmosphere influence on contact resistivity of ohmic Pd/Ge/Au contact to n-GaAs. Nanosystems: Physics, Chemistry, Mathematics, 2018, 9, 789-792.	0.4	4
14	Anodic processes in the chemical and electrochemical etching of Si crystals in acid-fluoride solutions: Pore formation mechanism. Semiconductors, 2017, 51, 458-472.	0.5	17
15	Effect of a wideband heteroepitaxial emitter on dynamics of turn-off switching of high-voltage power GaAs p-i-n diodes. Journal of Physics: Conference Series, 2016, 690, 012038.	0.4	1
16	Effect of nitride chemical passivation of the surface of GaAs photodiodes on their characteristics. Journal of Physics: Conference Series, 2016, 769, 012068.	0.4	0
17	Study of deep levels in GaAs pâ€“iâ€“n structures. Semiconductors, 2016, 50, 924-928.	0.5	9
18	GaSb-based photovoltaic laser-power converter for the wavelength Î» â‰ˆ 1550 nm. Semiconductors, 2015, 49, 1079-1082.	0.5	12

#	Article	IF	Citations
19	GaAs- A3B5heterostructures for high-speed power diodes manufacturing. Journal of Physics: Conference Series, 2015, 661, 012066.	0.4	0
20	Estimation of quality of GaAs substrates used for constructing semiconductor power devices. Technical Physics, 2014, 59, 1566-1569.	0.7	6
21	Defect engineering for carrier lifetime control in high voltage GaAs power diodes. , 2014, , .		7
22	Porous silicon and its applications in biology and medicine. Technical Physics, 2014, 59, 66-77.	0.7	55
23	Temperature stability of contact systems for GaSb-based photovoltaic converters. Semiconductors, 2014, 48, 1248-1253.	0.5	3
24	Surface of porous silicon under hydrophilization and hydrolytic degradation. Semiconductors, 2014, 48, 1211-1216.	0.5	12
25	GaAsâ€“AlGaAs heterostructure thyristors with completely optical transfer of emitter current. Semiconductors, 2011, 45, 515-518.	0.5	4
26	A decrease in ohmic losses and an increase in power in GaSb photovoltaic converters. Semiconductors, 2011, 45, 1219-1226.	0.5	11
27	Current flow mechanism in ohmic contact to n-4H-SiC. Semiconductors, 2010, 44, 463-466.	0.5	5
28	Fast pulsed gallium arsenide heterostructure diodes. Semiconductors, 2009, 43, 1055-1057.	0.5	12
29	Porous-Semiconductor-Based Hydrogen-Permeable Membrane. Industrial & Engineering Chemistry Research, 2007, 46, 2263-2267.	3.7	3
30	Control over carrier lifetime in high-voltage p-i-n diodes based on InxGa1-x As/GaAs heterostructures. Semiconductors, 2007, 41, 211-214.	0.5	10
31	Fast photonic switches based on GaAs nanostructures. Technical Physics Letters, 2006, 32, 372-376.	0.7	1
32	Deep-level centers in undoped p-GaAs layers grown by liquid phase epitaxy. Semiconductors, 2000, 34, 541-544.	0.5	7
33	Unstrained epitaxial InxGa1â^'x As films obtained on porous GaAs. Technical Physics Letters, 1999, 25, 852-854.	0.7	19
34	GaAs-Ge non-planar composite epitaxial heterostructures: LPE growth and cathodoluminescence investigations. , 0, , .		0
35	Effect of Neutron Irradiation on the Spectrum of Deep-Level Defects in GaAs Grown by Liquid-Phase Epitaxy in a Hydrogen and Argon Atmosphere. Semiconductors, 0, , .	0.5	1